1.5 A very low V_F MEGA Schottky barrier rectifiers

Rev. 03 — 15 January 2010

Product data sheet

Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifiers with an integrated guard ring for stress protection encapsulated in small and flat SMD plastic packages.

Table 1. Product overview

Type number	Package	Package		
	NXP	JEITA		
PMEG2015EH	SOD123F	-	single diode	
PMEG2015EJ	SOD323F	SC-90	single diode	
Features		人性性	WWW.DZSC.COM	

1.2 Features

Forward current: ≤ 1.5 A

Reverse voltage: ≤ 20 V

Very low forward voltage

Small and flat lead SMD plastic packages

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Inverse polarity protection
- Low and medium power general applications

1.4 Quick reference data

Quick reference data Table 2.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
l _F	forward current	$T_{sp} \le 55 ^{\circ}C$	-	-	1.5	Α
V_R	reverse voltage		-	-	20	V
V_{F}	forward voltage	$I_{\rm F} = 1.5 {\rm A}$	[1] -	560	660	mV

^[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.





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20 V, 1.5 A very low V_F MEGA Schottky barrier rectifiers

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline Symbol
1	cathode	[1]
2	anode	1 2 2 sym001

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 4. Ordering information

Type number	Package				
	Name	Description	Version		
PMEG2015EH	-	plastic surface mounted package; 2 leads	SOD123F		
PMEG2015EJ	SC-90	plastic surface mounted package; 2 leads	SOD323F		

4. Marking

Table 5. Marking codes

Type number	Marking code
PMEG2015EH	AD
PMEG2015EJ	EL

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	reverse voltage		-	20	V
I _F	forward current	$T_{sp} \le 55 ^{\circ}C$	-	1.5	Α
I _{FRM}	repetitive peak forward current	$t_p \le 1$ ms; $\delta \le 0.25$	-	5.5	Α
I _{FSM}	non-repetitive peak forward current	square wave; t _p = 8 ms	[1] -	9	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PMEG2015EH		<u>[1]</u> _	375	mW
			[2] _	830	mW
	PMEG2015EJ		<u>[1]</u> _	360	mW
			[2] _	830	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C

PMEG2015EH_EJ_3

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20 V, 1.5 A very low V_F MEGA Schottky barrier rectifiers

Table 6. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
T_{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air					
	PMEG2015EH		[1][2]	-	-	330	K/W
			[2][3]	-	-	150	K/W
	PMEG2015EJ		[1][2]	-	-	350	K/W
			[2][3]	-	-	150	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point						
	PMEG2015EH			-	-	60	K/W
	PMEG2015EJ			-	-	55	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage	$I_F = 10 \text{ mA}$	<u>[1]</u> -	240	270	mV
		$I_F = 100 \text{ mA}$	<u>[1]</u> -	300	350	mV
		$I_F = 500 \text{ mA}$	<u>[1]</u> -	400	460	mV
		I _F = 1 A	<u>[1]</u> -	480	550	mV
		I _F = 1.5 A	<u>[1]</u> -	560	660	mV
I _R	I _R reverse current	$V_R = 5 V$	-	5	10	μΑ
		V _R = 8 V	-	7	20	μΑ
		V _R = 10 V	-	8	30	μΑ
		V _R = 15 V	-	10	50	μΑ
		V _R = 20 V	-	15	70	μΑ
C _d	diode capacitance	$V_R = 1 V$; $f = 1 MHz$	-	40	50	pF
		1, ,				

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

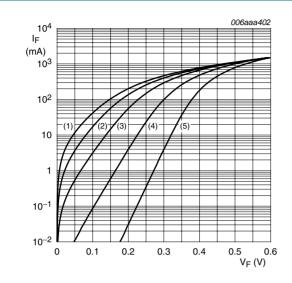
^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

^[2] For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and $I_{F(AV)}$ rating are available on request.

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

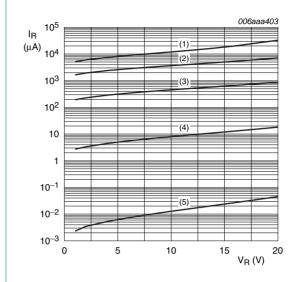
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20 V, 1.5 A very low V_F MEGA Schottky barrier rectifiers



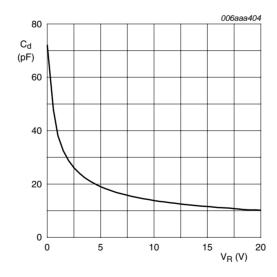
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Reverse current as a function of reverse voltage; typical values



 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz$

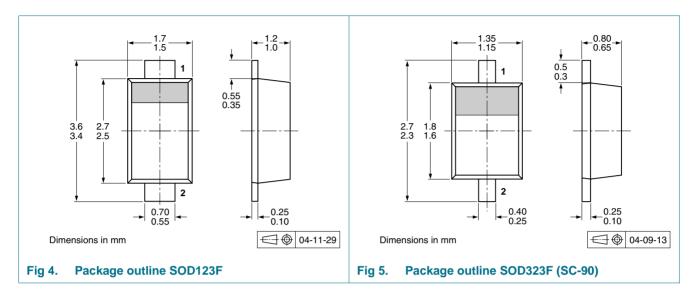
Diode capacitance as a function of reverse voltage; typical values Fig 3.

4 of 9

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20 V, 1.5 A very low V_F MEGA Schottky barrier rectifiers

8. Package outline



9. Packing information

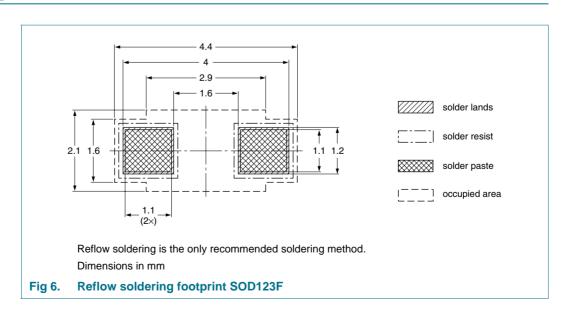
Table 9. Packing methods

The -xxx numbers are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity		
			3000	10000	
PMEG2015EH	SOD123F	4 mm pitch, 8 mm tape and reel	-115	-135	
PMEG2015EJ	SOD323F	_			

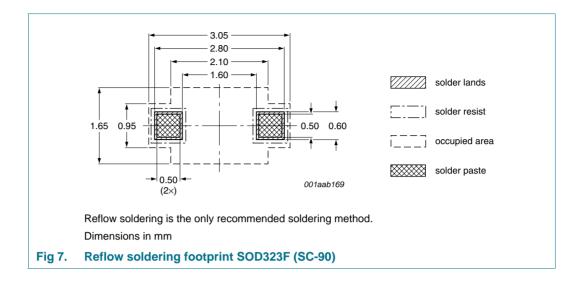
^[1] For further information and the availability of packing methods, see Section 13.

10. Soldering



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11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG2015EH_EJ_3	20100115	Product data sheet	-	PMEG2015EH_EJ_2
Modifications:		eet was changed to reflect w legal definitions and disc		
PMEG2015EH_EJ_2	20050407	Product data sheet	-	PMEG2015EJ_1
PMEG2015EJ_1	20050302	Product data sheet	-	-

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20 V, 1.5 A very low V_F MEGA Schottky barrier rectifiers

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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8 of 9

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20 V, 1.5 A very low V_F MEGA Schottky barrier rectifiers

14. Contents

1	Product profile	1
1.1	General description	1
1.2	Features	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	2
5	Limiting values	2
6	Thermal characteristics	3
7	Characteristics	3
8	Package outline	5
9	Packing information	5
10	Soldering	5
11	Revision history	7
12	Legal information	8
12.1	Data sheet status	8
12.2	Definitions	8
12.3	Disclaimers	8
12.4	Trademarks	8
13	Contact information	8
14	Contents	q

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